

SILICON PNP POWER TRANSISTOR

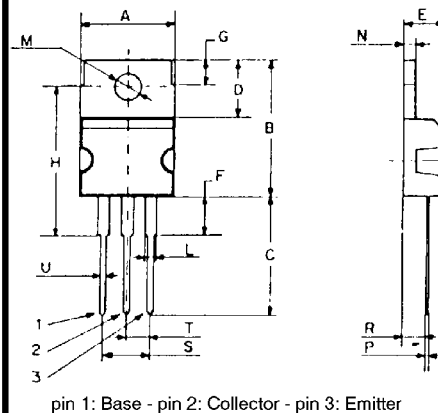
DESCRIPTION:

The **2N6132** is Designed for General Purpose Amplifier and Switching Applications.

MAXIMUM RATINGS

I_C	7.0 A (10 A PEAK)
I_B	3.0 A
V_{CE}	-40 V
P_{DISS}	50 W @ $T_C = 25^\circ\text{C}$
T_J	-65 °C to +150 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	2.5 °C/W

PACKAGE STYLE TO-220AB				
	DIMENSIONS			
	mm		inches	
	min	max	min	max
A	10	10.4	0.393	0.409
B	15.2	15.9	0.598	0.626
C	12.7	13.7	0.500	0.539
D	6.2	6.6	0.244	0.260
E	4.4	4.6	0.173	0.181
F	3.5	5.5	0.137	0.216
G	2.65	2.95	0.104	0.116
H	17.6 typ.		0.692 typ.	
L	1.14	1.7	0.044	0.067
M	3.75	3.85	0.147	0.151
N	1.23	1.32	0.048	0.051
P	0.41	0.64	0.016	0.025
R	2.4	2.72	0.094	0.107
S	4.95	5.15	0.194	0.203
T	2.4	2.7	0.094	0.106
U	0.61	0.94	0.024	0.037


CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 100\text{ mA}$	-40			V
I_{CEO}	$V_{CE} = -40\text{ V}$			2.0	mA
I_{CEX}	$V_{CE} = -40\text{ V}$ $V_{BE} = 1.5\text{ V}$ $T_C = 125^\circ\text{C}$			200 2.0	μA mA
I_{EBO}	$V_{EB} = -5.0\text{ V}$			1.0	mA
h_{FE}	$V_{CE} = -4.0\text{ V}$ $I_C = 2.5\text{ A}$ $I_C = 7.0\text{ A}$	20 7.0		100	---
$V_{CE(SAT)}$	$I_C = 7.0\text{ A}$ $I_B = 3.0\text{ A}$			-1.4	V
$V_{BE(ON)}$	$V_{CE} = -4.0\text{ V}$ $I_C = 2.5\text{ A}$			-2.0	V
h_{fe}	$V_{CE} = -4.0\text{ V}$ $I_C = 100\text{ mA}$ $f = 1.0\text{ KHz}$	25			---
f_t	$V_{CE} = -4.0\text{ V}$ $I_C = 1.0\text{ A}$ $f = 1.0\text{ MHz}$	2.5			MHz
C_{ob}	$V_{CB} = -10\text{ V}$ $f = 1.0\text{ MHz}$		300		pF